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IRF7319TRPBF

Data Sheet

30V Dual N- and P- Channel HEXFET Power MOSFET in a SO-8 package; Similar to IRF7319TR with Lead Free Packaging on Tape and Reel

Manufacturers	Infineon Technologies Corporation
Package/Case	SOIC-8
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRF7319TRPBF or Email to us: sales@ovaga.com We will contact you in 12 hours.

<u>RFQ</u>

General Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques.

- Generation V Technology
- Ultra Low On-Resistance
- Dual N and P Channel MOSFET
- Surface Mount
- Fully Avalanche Rated

Features

RoHS Compliant

Low RDS(on)

Dynamic dv/dt Rating

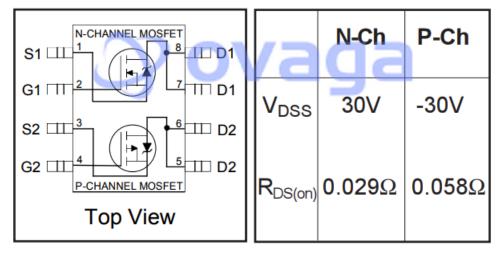
Fast Switching

Dual N and P-Channel MOSFET



IRF7319PbF

HEXFET® Power MOSFET



Related Products



IRLTS6342TRPBF

Infineon Technologies Corporation TSOP-6



IRF9310PBF Infineon Technologies Corporation SOIC-8



IRF9358TRPBF

Infineon Technologies Corporation SOP-8



IRFB3307ZPBF

Infineon Technologies Corporation **TO-220AB**



IRLHS6376TRPBF

Infineon Technologies Corporation PQFN2x2DD

IRFH9310TRPBF

Infineon Technologies Corporation POFN-8

IRFB7430PBF

Infineon Technologies Corporation TO-220

IRF7351TRPBF

Infineon Technologies Corporation SOIC-8



Ovaga Technologies Limited